



## Si4894BDY vs. Si4894DY

**Description:** N-Channel, 30 V (D-S) MOSFET

**Package:** SOIC-8

**Pin Out:** Identical

**Part Number Replacements:**

Si4894BDY-T1 Replaces Si4894DY-T1

Si4894BDY-T1-E3 (Lead (Pb)-free version) Replaces Si4894DY-T1-E3

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted				
Parameter	Symbol	Si4894BDY	Si4894DY	Unit
Drain-Source Voltage	$V_{DS}$	30	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	12	12.5	A
	$T_A = 70\text{ }^\circ\text{C}$	9.5	10	
Pulsed Drain Current	$I_{DM}$	40	20	
Continuous Source Current (MOSFET Diode Conduction)	$I_S$	2.3	2.7	
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	2.5	3.0	W
	$T_A = 70\text{ }^\circ\text{C}$	1.6	1.9	
Operating Junction and Storage Temperature Range	$T_j$ and $T_{stg}$	- 55 to 150	- 55 to 150	$^\circ\text{C}$
Maximum Junction-to-Ambient	$R_{thJA}$	50	42	$^\circ\text{C/W}$

<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted								
Parameter	Symbol	Si4894BDY			Si4894DY			Unit
		Min	Typ	Max	Min	Typ	Max	
<b>Static</b>								
Gate-Threshold Voltage	$V_{GS(th)}$	1.0		3.0	0.8			V
Gate-Body Leakage	$I_{GSS}$			$\pm 100$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$			1			1	$\mu\text{A}$
On-State Drain Current	$V_{GS} = 10\text{ V}$ $I_{D(on)}$	30			30			A
Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$ $r_{DS(on)}$		0.009	0.011		0.010	0.012	$\Omega$
	$V_{GS} = 4.5\text{ V}$		0.013	0.018		0.015	0.018	
Forward Transconductance	$g_{fs}$		32			30		S
Diode Forward Voltage	$V_{SD}$		0.76	1.1		0.7	1.1	V
<b>Dynamic</b>								
Total Gate Charge	$V_{GS} = 10\text{ V}$ $Q_g$		25.4	38		20	30	nC
	$V_{GS} = 5\text{ V}$		13.2	20		11.5	17	
Gate-Source Charge	$Q_{gs}$		5.3			3.0		
Gate-Drain Charge	$Q_{gd}$		4.3			4.5		
Gate Resistance	$R_g$	0.9	1.8	2.7	1		2.4	$\Omega$
<b>Switching</b>								
Turn-On Time	$t_{d(on)}$		13	20		10	20	ns
	$t_r$		10	15		5	10	
Turn-Off Time	$t_{d(off)}$		33	50		30	60	
	$t_f$		10	15		10	20	
Source-Drain Reverse Recovery Time	$t_{rr}$		25	40		30	60	

NS denotes parameter not specified in original data sheet.

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.